

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent No. 6,734,468

Allowed: January 2, 2004

Toshiya Uemura et al.

Serial No.: 08/866,129

Filed: May 30, 1997



Group Art Unit: 2814

Examiner: Douglas A. Wille

For: DEVICES RELATED TO ELECTRODE PADS FOR P-TYPE GROUP III NITRIDE COMPOUND SEMICONDUCTORS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Certificate
JUN 23 2004
of Correction

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

The undersigned respectfully requests a Certificate of Correction for the above-identified patent. In particular, it is requested that claim 4 and claim 8 be respectively corrected to read :

4. The light-emitting semiconductor device according to claim 1, wherein said electrode layer has a multi-layer structure having at least a first electrode layer formed on said surface layer and a second electrode layer formed on said first electrode layer, wherein said first electrode layer comprises material having an ionization potential that is lower than that of said second electrode layer, said material of said second electrode layer, has an ohmic characteristic to said surface layer better than that of said first electrode layer, and said material of said second electrode layer being distributed more deeply into said surface layer than that of said first electrode layer by heat treatment.

8. The light-emitting semiconductor device according to claim 1, further comprising:

semiconductor layers having Group III nitride compound semiconductor and satisfying the formula, $A_{1-x}Ga_xIn_{1-x-y}N_{1-y}$ Δ $Al_xGa_{1-x-y}In_{1-x-y}N_{1-y}$, wherein $0 < x < 1$, $0 < y < 1$, and $0 < x + y < 1$, $0 < x - y < 1$ $0 < x + y < 1$.

JUN 23 2004

Please forward a Certificate of Correction to the address shown below. If there are any questions on this matter, please direct all telephone calls to the number shown below.

Since these errors were due to the U.S.P.T.O, no fee is believed due or is submitted herewith.

The Commissioner is authorized charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,



Sean M. McGinn, Esq.
Reg. No. 34,386

Date: 6/18/04
McGinn & Gibb, PLLC
Intellectual Property Law
8321 Old Courthouse Road, Suite 200
Vienna, VA 22182-3817
(703) 761-4100
Customer No. 21254

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,734,468 *02*
DATED : May 11, 2004
INVENTOR(S) : Toshiya Uemura et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

4. The light-emitting semiconductor device according to claim 1, wherein said electrode layer has a multi-layer structure having at least a first electrode layer formed on said surface layer and a second electrode layer formed on said first electrode layer, wherein said first electrode layer comprises material having an ionization potential that is lower than that of said second electrode layer, said material of said second electrode layer, has an ohmic characteristic to said surface layer better than that of said first electrode layer, and said material of said second electrode layer being distributed more deeply into said surface layer than that of said first electrode layer by heat treatment.

8. The light-emitting semiconductor device according to claim 1, further comprising:
semiconductor layers having Group III nitride compound semiconductor and satisfying the formula, $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$, wherein $0 < x < 1$, $0 < y < 1$, and $0 < x + y < 1$, and $0 < x + y < 1$.

MAILING ADDRESS OF SENDER:

Sean M. McGinn
Registration No. 34,386
McGinn & Gibb, PLLC
8321 Old Courthouse Road
Suite 200
Vienna, VA 22182-3817
Customer No. 21254

PATENT NO. 6,734,468 *02*

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